

Amendments to the Specification:

Please replace the paragraph beginning at page 4, line 22, with the following rewritten paragraph:

It is another feature of the present invention to add a material selected from the group consisting of Ni, Pd, Pt, Cu, Ag, Au, In, Sn, ~~Pd, Sn~~, P, As, and Sb into a silicon semiconductor film at a trace amount by contacting a solution containing said material with the silicon film and then crystallize the silicon semiconductor film by heating at a relatively low temperature.

Please replace the paragraph bridging pages 7 and 8 with the following rewritten paragraph:

In the foregoing examples, the nickel can be completely ~~[[solved]]~~ dissolved by the solvent. However, even if the nickel is not completely ~~[[solved]]~~ dissolved, it is possible to use a material such as an emulsion in which elemental nickel or nickel compound is dispersed uniformly in a dispersion medium.

Please replace the paragraph beginning at page 9, line 16, with the following rewritten paragraph:

The use of nickel as the catalyst element is particularly effective in the process according to the present invention. However, other useful catalyst elements include nickel (Ni), palladium (Pd), platinum (Pt), copper (Cu), silver (Ag), gold (Au), indium (In), tin (Sn), phosphorus (P), arsenic (As), and antimony (Sb). Otherwise, the catalyst element may be at least one selected from the elements belonging to the Group ~~VIII, IIIb, IVb, and Vb~~ IIIa, IVa and Va of the periodic table.

Please replace the paragraph beginning at page 14, line 9, with the following rewritten paragraph:

From the foregoing facts, it can be concluded that the surface of the lateral growth region 25 has a plane ~~which is perpendicular to the [111] direction, namely at least one of planes {111} and those expressed by {hkl} (h+k=l), for example, {110}, {123}, {134}, {235}, {145}, {156}, {257}, or {167}, or the neighborhood thereof.~~

Please replace the paragraph beginning at page 18, line 18, with the following rewritten paragraph:

The resulting amorphous silicon film having the oxide film thereon is coated with an aqueous acetate solution containing nickel at a concentration of 10 ppm. The resulting structure is retained for a duration of 5 minutes, and is subjected thereafter to spin drying using a spinner. The silicon oxide film is removed thereafter using a ~~[[buffered]]~~ buffered hydrofluoric acid, and a silicon film is crystallized by heating the resulting structure at 550 °C for a duration of 4 hours. The process up to this step is the same as that described in Example 1.